

# **isc Silicon NPN Power Transistor**

### **DESCRIPTION**

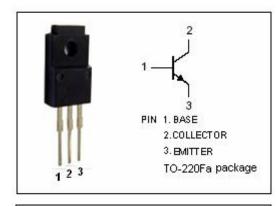
- · Low Collector Saturation Voltage
  - : V<sub>CE(sat)</sub>= 1.0V(Max)@ I<sub>C</sub>= 2A
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 60V (Min)
- · Good Linearity of hFE
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

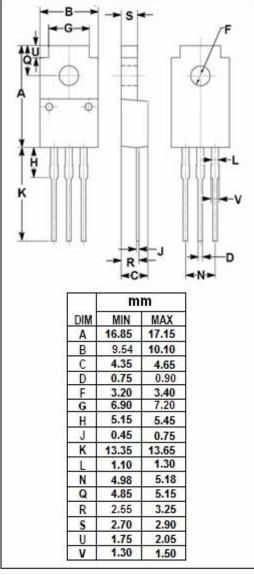


· Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	80	V	
Vceo	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
I <sub>C</sub>	Collector Current-Continuous	4	А	
lΒ	Base Current-Peak	1	А	
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25°C	30	W	
	Collector Power Dissipation @ T <sub>a</sub> =25℃	2	VV	
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	Range -55~150		







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2SD1475

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

10-23 C unless otherwise specified								
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	60			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.0	V		
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V			1.2	V		
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 80V; I <sub>E</sub> = 0			100	μА		
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			100	μА		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	40		320			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	20					
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 12V		50		MHz		
Switching times								
t <sub>on</sub>	Turn-on Time			0.35		μS		
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 4A; I <sub>B1</sub> = I <sub>B2</sub> = 0.4A		1.0		μS		
t <sub>f</sub>	Fall Time			0.3		μ <b>S</b>		

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